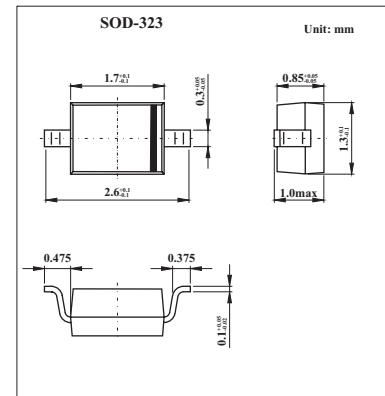


## Silicon Epitaxial Planar Diode

## 1SV302

## ■ Features

- High Capacitance Ratio:  $C_{2V}/C_{25V}=17.5$ (Typ.)
- Low Series Resistance:  $r_s=1.05 \Omega$  (Typ.)
- Useful for Small Size Tuner

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Value	Unit
Reverse Voltage	$V_R$	30	V
Peak Reverse Voltage	$V_{RM}$	35( $R_L = 10K \Omega$ )	V
Junction Temperature	$T_j$	125	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	-55 to +125	$^\circ\text{C}$

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse Voltage	$V_R$	$I_R = 1 \mu\text{A}$	30			V
Reverse Current	$I_R$	$V_R = 28 \text{V}$			10	nA
Capacitance	$C_{2V}$	$f = 1 \text{MHz}; V_R = 2 \text{V}$	42	47	51	pF
	$C_{25V}$	$f = 1 \text{MHz}; V_R = 25 \text{V}$	2.1	2.6	3.1	
Capacitance Ratio	$C_{2V}/C_{25V}$		17	17.5		
Series Resistance	$r_s$	$V_R = 5 \text{V}, f = 470 \text{MHz}$		1.05	1.25	$\Omega$

Note :

Available in matched group for capacitance to 2.5%.

$$\frac{C(\text{Max.})-C(\text{Min.})}{C(\text{Min.})} \leq 0.025$$

( $V_R=2\sim 25\text{V}$ )

## ■ Marking

Marking	TT